

## 1. General description

Planar passivated Silicon Controlled Rectifier (SCR) in a SOT78 (TO-220AB) plastic package intended for use in applications requiring very high inrush current capability, high thermal cycling performance and high junction temperature capability ( $T_{j(max)} = 150\text{ °C}$ ).

## 2. Features and benefits

- High junction operating temperature capability ( $T_{j(max)} = 150\text{ °C}$ )
- Very high current surge capability
- Planar passivated for voltage ruggedness and reliability
- High turn-on current rise  $di_T/dt = 100\text{ A}/\mu\text{s}$
- High noise immunity  $dV_p/dt = 500\text{ V}/\mu\text{s}$  up to  $150\text{ °C}$
- High thermal cycling performance
- High voltage capability

## 3. Applications

- Ignition circuits
- Protection circuits e.g. SMPS inrush current
- Motor control circuits and starters
- Voltage regulation
- Solid state relays
- High junction operating temperature capability ( $T_{j(max)} = 150\text{ °C}$ )

## 4. Quick reference data

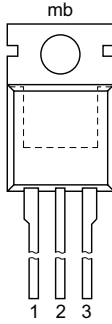

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values	Unit
<b>Absolute maximum rating</b>				
$V_{DRM}$	repetitive peak off-state voltage		800	V
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{mb} \leq 128\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	40	A
$I_{TSM}$	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 10\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	450	A
		half sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 8.3\text{ ms}$	495	A
$T_j$	junction temperature		150	°C

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	-	-	15	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>	-	-	60	mA
$V_T$	on-state voltage	$I_T = 80\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 10</a>	-	-	1.6	V
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$ ; $T_j = 150\text{ °C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit	500	-	-	V/ $\mu$ s

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		 sym037
2	A	anode		
3	G	gate		
mb	A	mounting base; connect to anode		

## 6. Ordering information

Table 3. Ordering information

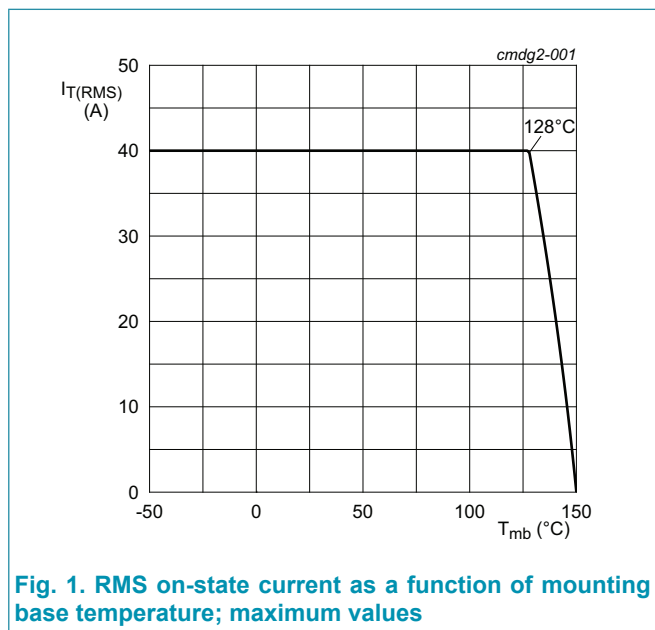
Type number	Package		Version
	Name	Description	
TYN40-800T	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

## 7. Limiting values

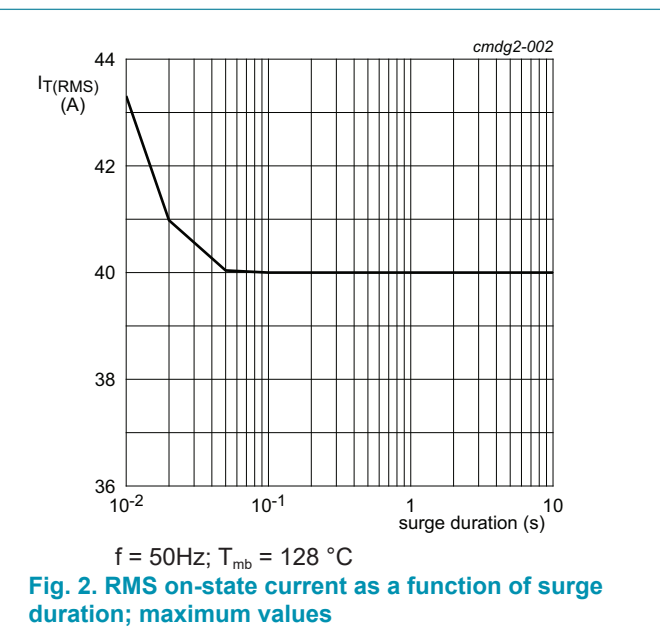
**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

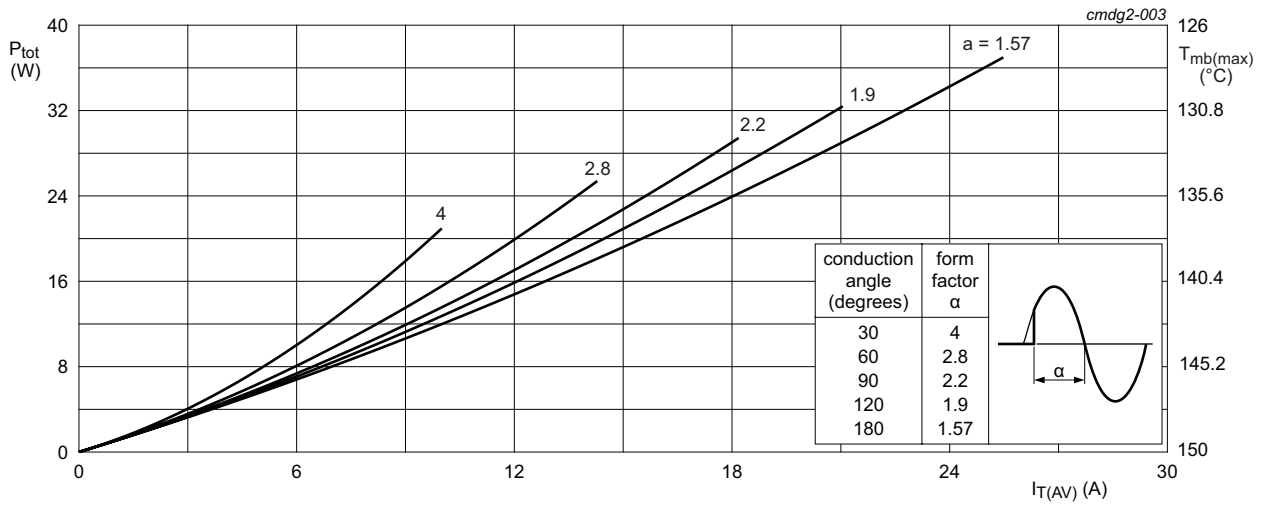
Symbol	Parameter	Conditions	Values	Unit
$V_{DRM}$	repetitive peak off-state voltage		800	V
$V_{RRM}$	repetitive peak reverse voltage		800	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_{mb} \leq 128^\circ\text{C}$ ;	25	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{mb} \leq 128^\circ\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	40	A
$I_{TSM}$	non-repetitive peak on-state current	half sine wave; $T_{j(\text{init})} = 25^\circ\text{C}$ ; $t_p = 10\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	450	A
		half sine wave; $T_{j(\text{init})} = 25^\circ\text{C}$ ; $t_p = 8.3\text{ ms}$	495	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ms}$ ; sine wave	1012.5	$\text{A}^2\text{s}$
$di_T/dt$	rate of rise of on-state current	$I_G = 30\text{mA}$	100	$\text{A}/\mu\text{s}$
$I_{GM}$	peak gate current		5	A
$V_{GM}$	peak gate voltage		5	V
$P_{GM}$	peak gate power		20	W
$P_{G(AV)}$	average gate power	over any 20 ms period	0.5	W
$T_{stg}$	storage temperature		-40 to 150	$^\circ\text{C}$
$T_j$	junction temperature		150	$^\circ\text{C}$



**Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values**

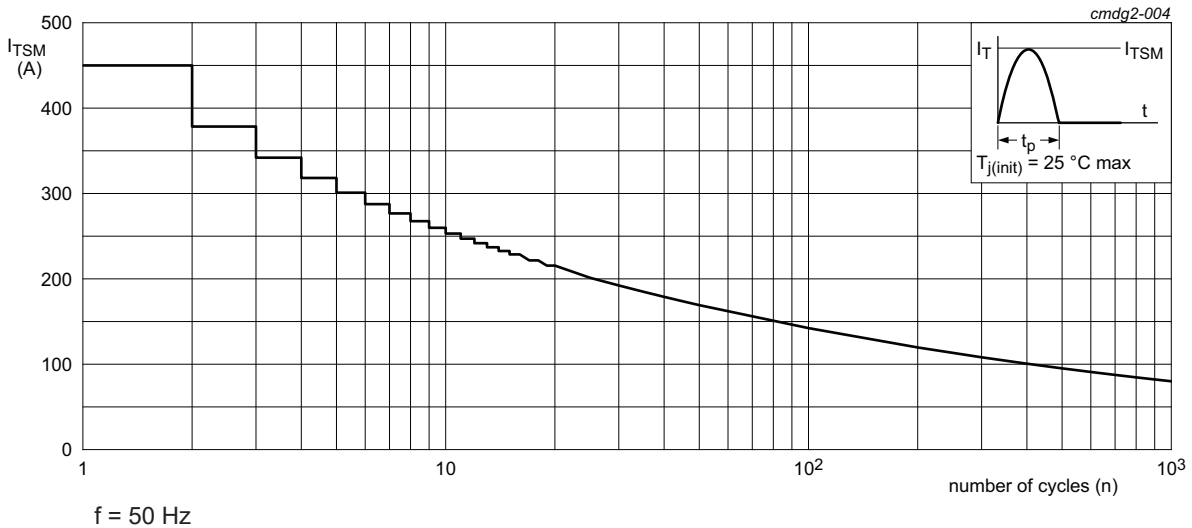


**Fig. 2. RMS on-state current as a function of surge duration; maximum values**



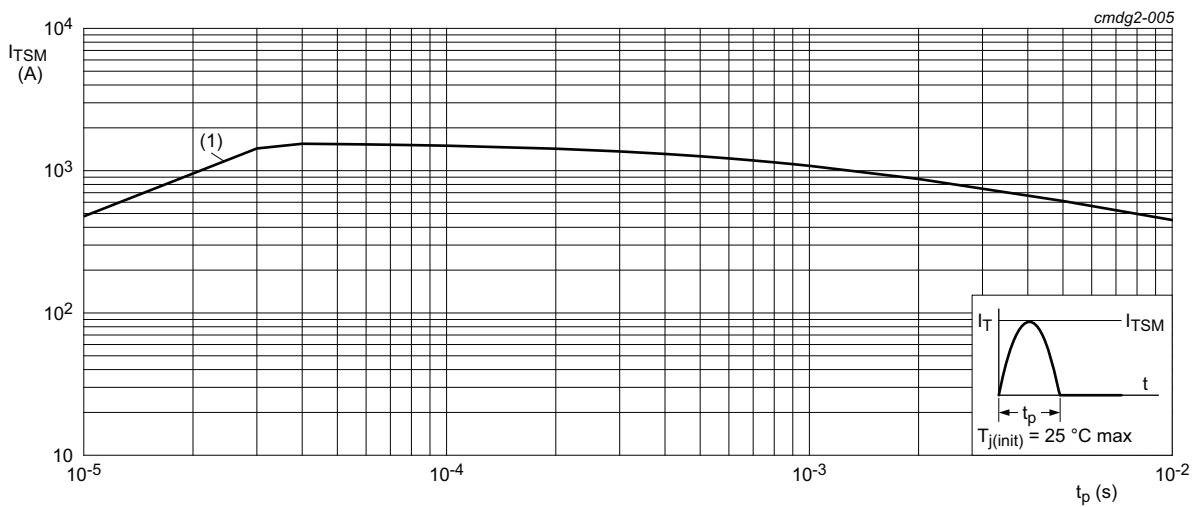
$\alpha$  = conduction angle  
 $a$  = form factor =  $I_{T(RMS)} / I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



$t_p \leq 10$  ms ;  
 (1)  $dI_T/dt$  limit

Fig. 5. Total power dissipation as a function of RMS on-state current; maximum values

## 8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	<a href="#">Fig. 6</a>	-	-	0.6	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

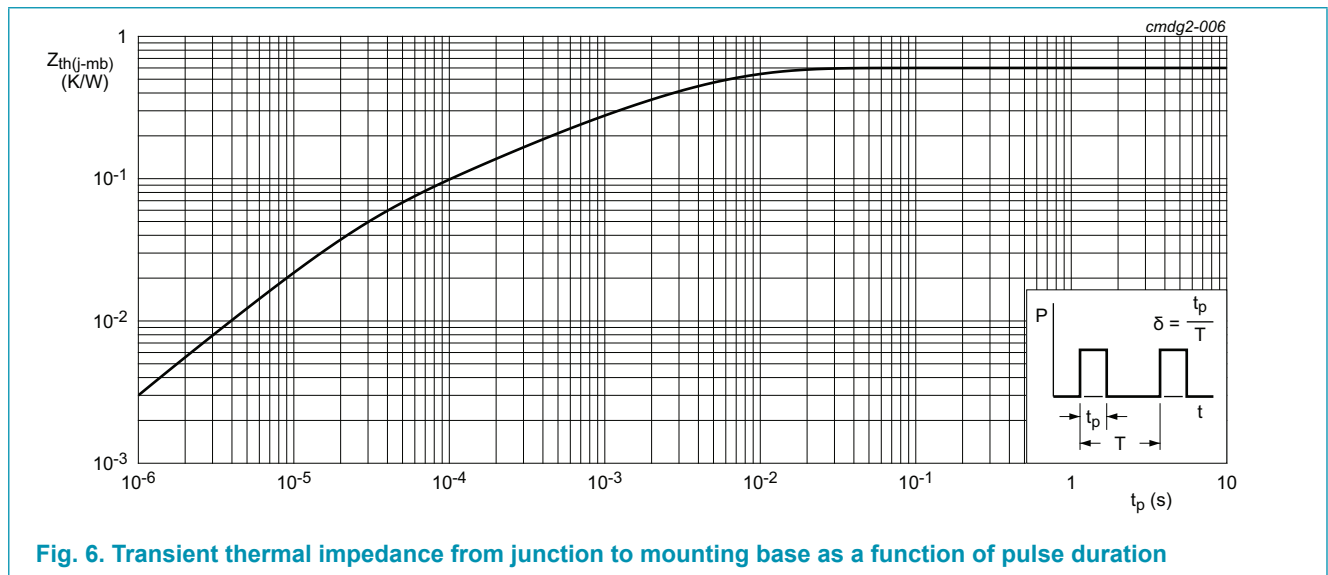


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	-	-	15	mA
$I_L$	latching current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 8</a>	-	-	80	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 9</a>	-	-	60	mA
$V_T$	on-state voltage	$I_T = 80\text{ A}$ ; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 10</a>	-	-	1.6	V
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_J = 25\text{ °C}$ ; <a href="#">Fig. 11</a>	-	0.7	1.2	V
		$V_D = 400\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_J = 150\text{ °C}$ ; <a href="#">Fig. 11</a>	0.25	0.5	-	V
$I_D$	off-state current	$V_D = 800\text{ V}$ ; $T_J = 150\text{ °C}$	-	-	2	mA
$I_R$	reverse current	$V_D = 800\text{ V}$ ; $T_J = 150\text{ °C}$	-	-	2	mA
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$ ; $T_J = 150\text{ °C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit	500	-	-	V/ $\mu$ s
$t_{gt}$	gate-controlled turn-on time	$I_{TM} = 80\text{ A}$ ; $V_D = 800\text{ V}$ ; $I_G = 100\text{ mA}$ ; $(dI_G/dt)_M = 0.2\text{ A}/\mu\text{s}$ ; $T_J = 25\text{ °C}$	-	2	-	$\mu$ s
$t_q$	commutated turn-off time	$V_{DM} = 536\text{ V}$ ; $T_J = 150\text{ °C}$ ; $I_{TM} = 40\text{ A}$ ; $V_R = 25\text{ V}$ ; $dV_D/dt = 50\text{ V}/\mu\text{s}$ ; $(dI_T/dt)_M = 30\text{ A}/\mu\text{s}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ )	-	70	-	$\mu$ s

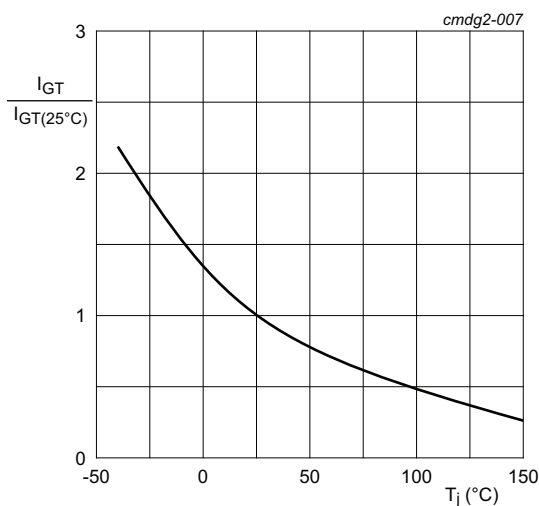


Fig. 7. Normalized gate trigger current as a function of junction temperature

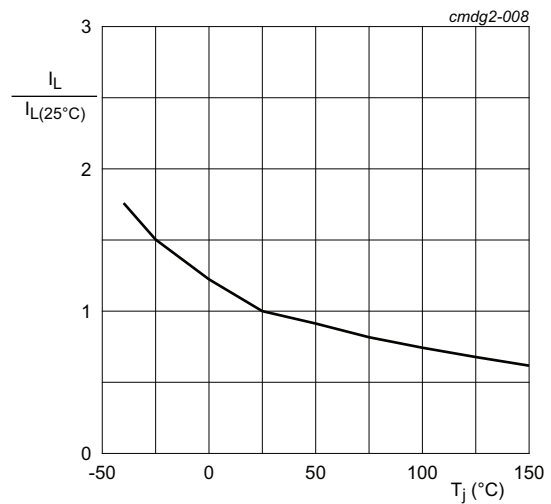


Fig. 8. Normalized latching current as a function of junction temperature

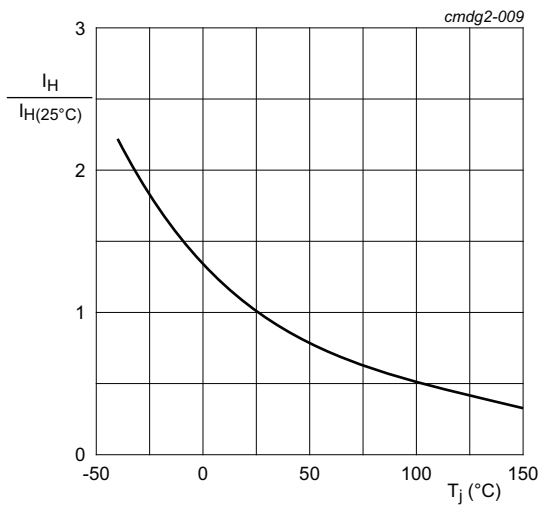
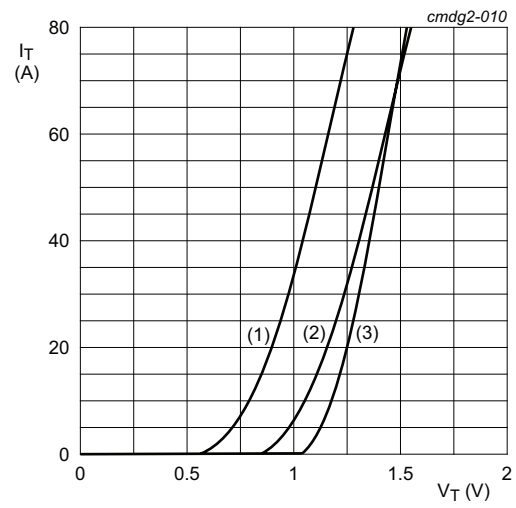


Fig. 9. Normalized holding current as a function of junction temperature



$V_o = 1.036 \text{ V}; R_s = 0.0066 \Omega$   
 (1)  $T_j = 150^\circ\text{C}$ ; typical values  
 (2)  $T_j = 150^\circ\text{C}$ ; maximum values  
 (3)  $T_j = 25^\circ\text{C}$ ; maximum values

Fig. 10. On-state current as a function of on-state voltage

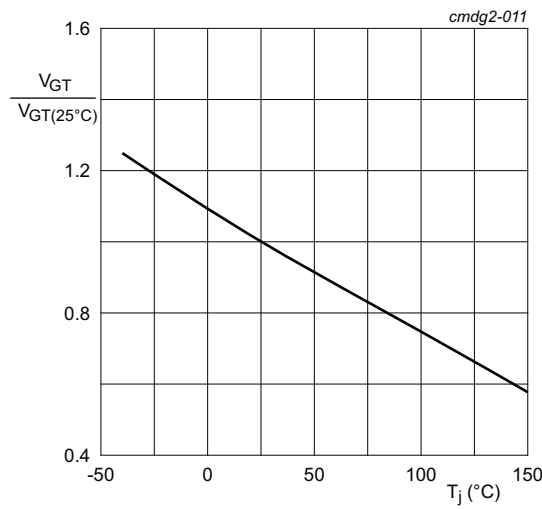
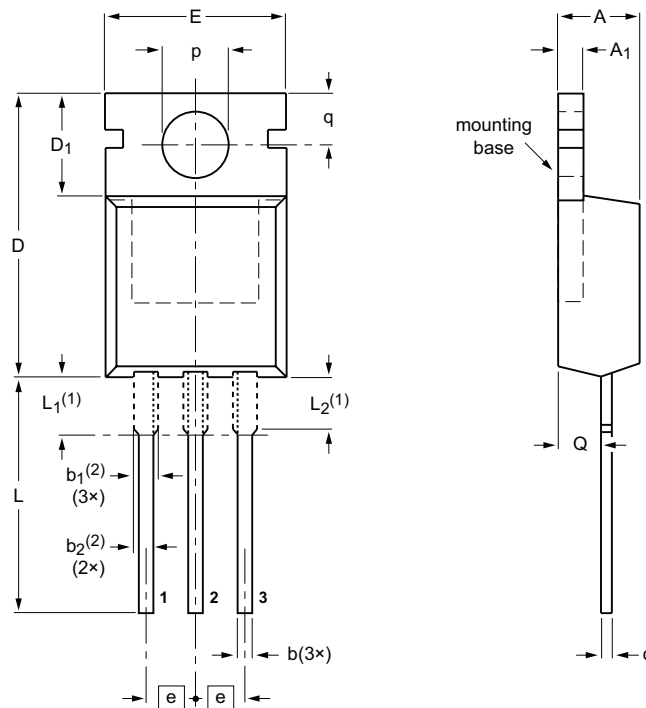


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

### 10. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78



**DIMENSIONS (mm are the original dimensions)**

UNIT	A	A <sub>1</sub>	b	b <sub>1</sub> ( <sup>2</sup> )	b <sub>2</sub> ( <sup>2</sup> )	c	D	D <sub>1</sub>	E	e	L	L <sub>1</sub> ( <sup>1</sup> )	L <sub>2</sub> ( <sup>1</sup> ) max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

**Notes**

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13

Fig. 12. Package outline TO-220AB (SOT78)



## 11. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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